Abstracts

Propagation Characteristics of Lossy Distributed GaAs FET Structures

F. Alessandri, G. Baini, G. D'Inzeo and R. Sorrentino. "Propagation Characteristics of Lossy Distributed GaAs FET Structures." 1992 MTT-S International Microwave Symposium Digest 92.2 (1992 Vol. II [MWSYM]): 963-966.

The generalized transverse resonance technique is applied to compute the propagation characteristics of distributed FET structures. To account for conductor thickness of the order or less than the skin depth, a modified perturbational approach is applied, which yields very accurate results with negligible computational effort. Loss behaviors of the three dominant modes and the contributions of the various electrodes to the total loss have been investigated.

❑ Return to main document.